

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
1	IS&R	L1	2	("5866945").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/12 23:21			
2	IS&R	L2	2	("5721601").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/12 23:21			
3	IS&R	L3	2	("5796150").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/12 23:22			
4	IS&R	L4	2	("6350673").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/12 23:24			
5	BRS	L5	1	2000- 149535.NRAN.	DERWENT	2005/06/12 23:23			
6	BRS	L10	2	"07074167"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:20			
7	BRS	L11	65	aluminum adj annealing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:21			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
8	BRS	L12	1	aluminum adj annealing and (h2 or hydrogen) near diffus\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:22			
9	BRS	L13	467	(h2 or hydrogen) near diffus\$5 with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 01:14			
10	BRS	L14	50	(h2 or hydrogen) near diffus\$5 near semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:23			
11	BRS	L15	1	(h2 or hydrogen) near diffus\$5 near semiconductor and hsq	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:23			
12	BRS	L16	20	(h2 or hydrogen) near diffus\$5 with semiconductor and hsq	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:24			
13	BRS	L17	19	(h2 or hydrogen) near diffus\$5 with semiconductor and hsq and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:27			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
14	BRS	L20	93	(h2 or hydrogen) with plasma with diffus\$5 with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:30			
15	BRS	L21	2	(h2 or hydrogen) with plasma with diffus\$5 with teos with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:29			
16	BRS	L22	12	(h2 or hydrogen) with plasma with diffus\$5 with semiconductor and planar\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:36			
17	BRS	L23	59	(h2 or hydrogen) with plasma with diffus\$5 and semiconductor and planariz\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:38			
18	BRS	L24	1	(h2 or hydrogen) with plasma with diffus\$5 same semiconductor same planariz\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:37			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Com men ts	Er ro r De fi ni ti on	Er ro rs
19	BRS	L25	54	(h2 or hydrogen) with plasma with diffus\$5 and semiconductor and planariz\$ and metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:38			
20	BRS	L26	2	(h2 or hydrogen) with plasma with diffus\$5 with planariz\$ and metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:39			
21	BRS	L27	11	(h2 or hydrogen) near plasma with diffus\$5 and planariz\$ and metal and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:45			
22	BRS	L28	100	(h2 or hydrogen) near plasma near (diffus\$5 or treat\$5) and planariz\$ and metal and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:46			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
23	BRS	L29	9	(h2 or hydrogen) near plasma with diffus\$5 with treat\$5 and planariz\$ and metal and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:47			
24	BRS	L30	0	(h2 or hydrogen) near plasma with diffus\$5 with treat\$5 and planariz\$ and metal and semiconductor and ic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:47			
25	BRS	L31	0	(h2 or hydrogen) near plasma with diffus\$5 with treat\$5 and planariz\$ and metal and ic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:47			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
26	BRS	L32	4	(h2 or hydrogen) near plasma with diffus\$5 with treat\$5 and planariz\$ and metal and (ic or integrat\$4 near circuit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:48			
27	BRS	L33	83	(h2 or hydrogen) with diffus\$5 with treat\$5 and planariz\$ and metal and (ic or integrat\$4 near circuit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:49			
28	BRS	L34	83	(h2 or hydrogen) with diffus\$5 with treat\$5 and planariz\$ and metal and (ic or integrat\$4 near circuit) and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:49			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
29	BRS	L35	14	(h2 or hydrogen) with diffus\$5 with treat\$5 with plasma and planariz\$ and metal and (ic or integrat\$4 near circuit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:49			
30	BRS	L36	176	("438"/\$).ccls. and (h2 or hydrogen) near diffus\$5 with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 00:59			
31	BRS	L37	66	("438"/\$).ccls. and (h2 or hydrogen) near diffus\$5 with semiconductor and (planariz\$ or hsq or sog)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 01:01			
32	BRS	L38	86	("257"/\$).ccls. and (h2 or hydrogen) near diffus\$5 with semiconductor and (planariz\$ or hsq or sog)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 01:09			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
33	BRS	L39	21	(h2 or hydrogen) near diffus\$5 with semiconductor and (hsq or hydrogen adj silsesquioxane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/13 01:14			
34	BRS	L40	1	1996-261922.NRAN.	DERWENT	2005/06/13 01:16			